

1N4614 THRU 1N4627

SILICON ZENER DIODE
LOW NOISE
1.8 VOLT THRU 6.2 VOLT
250mW, 5% TOLERANCE



DO-35 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 1N4614 series silicon Zener diode is designed for low leakage, low current, and low noise applications. Higher voltage devices are available in the 1N4099 series.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Power Dissipation

Operating and Storage Junction Temperature

SYMBOL

P_D

T_J, T_{stg}

250

-65 to +200

UNITS

mW

$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$) $V_F=1.0\text{V MAX @ } I_F=200\text{mA}$ (for all types)

TYPE	ZENER VOLTAGE $V_Z @ I_{ZT}$			TEST CURRENT	MAXIMUM ZENER IMPEDANCE	MAXIMUM REVERSE CURRENT		MAXIMUM ZENER CURRENT	MAXIMUM NOISE DENSITY
	MIN	NOM	MAX	I_{ZT}	$Z_{ZT} @ I_{ZT}$	$I_R @ V_R$		I_{ZM}	$N_D @ 250\mu\text{A}$
	V	V	V	μA	Ω	μA	V	mA	$\mu\text{V}/\sqrt{\text{Hz}}$
1N4614	1.710	1.8	1.890	250	1200	7.5	1.0	120	1.0
1N4615	1.900	2.0	2.100	250	1250	5.0	1.0	110	1.0
1N4616	2.090	2.2	2.310	250	1300	4.0	1.0	100	1.0
1N4617	2.280	2.4	2.520	250	1400	2.0	1.0	95	1.0
1N4618	2.565	2.7	2.835	250	1500	1.0	1.0	90	1.0
1N4619	2.850	3.0	3.150	250	1600	0.8	1.0	85	1.0
1N4620	3.135	3.3	3.465	250	1650	7.5	1.5	80	1.0
1N4621	3.420	3.6	3.780	250	1700	7.5	2.0	75	1.0
1N4622	3.705	3.9	4.095	250	1650	5.0	2.0	70	1.0
1N4623	4.085	4.3	4.515	250	1600	4.0	2.0	65	1.0
1N4624	4.465	4.7	4.935	250	1550	10	3.0	60	1.0
1N4625	4.845	5.1	5.355	250	1500	10	3.0	55	2.0
1N4626	5.320	5.6	5.880	250	1400	10	4.0	50	4.0
1N4627	5.890	6.2	6.510	250	1200	10	5.0	45	5.0

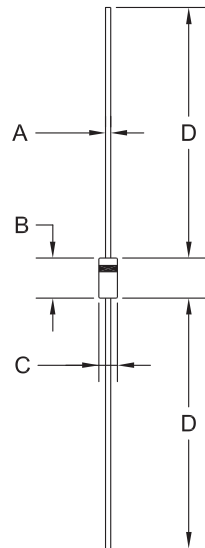
R3 (1-May 2013)

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DO-35 CASE - MECHANICAL OUTLINE



R1

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.018	0.022	0.46	0.56
B	0.120	0.200	3.05	5.08
C	0.060	0.090	1.52	2.29
D	1.000	-	25.40	-

DO-35 (REV: R1)

MARKING: FULL PART NUMBER

R3 (1-May 2013)